**IN THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

1-5. (Canceled)

6. (Currently Amended) A transistor comprising:

a channel region; and

at least one of a source region and a drain region having a first ~~source~~ crystalline portion adjacent to the channel region and a second ~~source~~ crystalline portion adjacent to the first ~~source~~ crystalline portion, ~~said second source portion comprising a metal advanced crystallization region; and~~

~~a drain region having a first drain portion adjacent to the channel region and a second drain portion adjacent to the first drain portion,~~

wherein ~~the channel region and at least one of the first source portion and the first drain portion comprise a metal advanced lateral crystallization region~~ the second crystalline portion is a region where a metal was directly added, and

wherein the first crystalline portion is a region where crystallization advanced from the second crystalline portion.

7-13. (Canceled)

14. (New) A transistor comprising:

a channel region; and

at least one of a source region and a drain region having a first crystalline portion adjacent to the channel region and a second crystalline portion adjacent to the first crystalline portion,

wherein the second crystalline portion has a surface through which a metal is added, and

wherein the first crystalline portion is a region where crystallization advanced from the second crystalline portion.

15. (New) A transistor comprising:

a channel region; and

at least one of a source region and a drain region having a first crystalline portion adjacent to the channel region and a second crystalline portion adjacent to the first crystalline portion,

wherein the second crystalline portion is a region where a metal was directly added,

wherein the first crystalline portion is a region where crystallization advanced from the second crystalline portion, and

wherein a crystal of the first crystalline portion is a crystal which grew in a horizontal direction from the second crystalline portion.

16. (New) A transistor comprising:

a channel region; and

at least one of a source region and a drain region having a first crystalline portion adjacent to the channel region and a second crystalline portion adjacent to the first crystalline portion,

wherein the second crystalline portion has a surface through which a metal is added, and

wherein the first crystalline portion is a region where crystallization advanced from the second crystalline portion, and

wherein a crystal of the first crystalline portion is a crystal which grew in a horizontal direction from the second crystalline portion.

17. (New) The transistor according to claim 6, further comprising:

a third crystalline portion between the channel region and the first crystalline portion;

a gate insulating film; and

a gate electrode adjacent to the channel region and the third crystalline portion with the gate insulating film interposed therebetween.

18. (New) The transistor according to claim 6, further comprising:

a gate insulating film over the channel region, the first crystalline portion, and the second crystalline portion,

wherein the gate insulating film has an opening overlapping with the second crystalline portion.

19. (New) The transistor according to claim 6,

wherein the metal is nickel.

20. (New) The transistor according to claim 6,

wherein the metal is at least one from the group consisting of nickel, iron, cobalt, platinum, and palladium.

21. (New) The transistor according to claim 14, further comprising:

a third crystalline portion between the channel region and the first crystalline portion;

a gate insulating film; and

a gate electrode adjacent to the channel region and the third crystalline portion with the gate insulating film interposed therebetween.

22. (New) The transistor according to claim 14, further comprising:

a gate insulating film over the channel region, the first crystalline portion, and the second crystalline portion,

wherein the gate insulating film has an opening overlapping with the second crystalline portion.

23. (New) The transistor according to claim 14,

wherein the metal is nickel.

24. (New) The transistor according to claim 14,

wherein the metal is at least one from the group consisting of nickel, iron, cobalt, platinum, and palladium.

25. (New) The transistor according to claim 15, further comprising:

a third crystalline portion between the channel region and the first crystalline portion;

a gate insulating film; and

a gate electrode adjacent to the channel region and the third crystalline portion with the gate insulating film interposed therebetween.

26. (New) The transistor according to claim 15, further comprising

a gate insulating film over the channel region, the first crystalline portion, and the second crystalline portion,

wherein the gate insulating film has an opening overlapping with the second crystalline portion.

27. (New) The transistor according to claim 15,

wherein the metal is nickel.

28. (New) The transistor according to claim 15,

wherein the metal is at least one from the group consisting of nickel, iron, cobalt, platinum, and palladium.

29. (New) The transistor according to claim 16, further comprising:

a third crystalline portion between the channel region and the first crystalline portion;

a gate insulating film; and

a gate electrode adjacent to the channel region and the third crystalline portion with the gate insulating film interposed therebetween.

30. (New) The transistor according to claim 16, further comprising:

a gate insulating film over the channel region, the first crystalline portion, and the second crystalline portion,

wherein the gate insulating film has an opening overlapping with the second crystalline portion.

31. (New) The transistor according to claim 16,

wherein the metal is nickel.

32. (New) The transistor according to claim 16,

wherein the metal is at least one from the group consisting of nickel, iron, cobalt, platinum, and palladium